

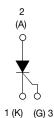
VS-16TTS...FPPbF Series, VS-16TTS...FP-M3 Series

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Vishay Semiconductors

High Voltage Phase Control Thyristor, 16 A





TO-220AB FULL-PAK

Diode variation

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FEATURES

- Designed and qualified for industrial level
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 approved
- Compliant to RoHS Directive 2002/95/EC
- 125 °C max. operating junction temperature
- Halogen-free according to IEC 61249-2-21 definition (-M3 only)







PRODUCT SUMMARY	APPLICATIONS	
Package	TO-220FP	 Typical usage is ir

Single SCR

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

I _{T(AV)}	10 A
V _{DRM} /V _{RRM}	800 V, 1200 V
V_{TM}	1.4 V
I _{GT}	60 mA
T_J	- 40 °C to 125 °C

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А			

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	10	^		
I _{RMS}		16	A		
V _{DRM} /V _{RRM}		800/1200	V		
I _{TSM}		200	А		
V _T	10 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/μs		
TJ	Range	- 40 to 125	°C		

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA		
VS-16TTS08FPPbF, VS-16TTS08FP-M3	800	800	10		
VS-16TTS12FPPbF, VS-16TTS12FP-M3	1200	1200	10		



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	
PANAMETER	STIVIBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 95 °C,	180° conduction, half sine wave	1	0	
Maximum RMS on-state current	I _{RMS}			1	6	А
Maximum peak, one-cycle,	L	10 ms sine p	oulse, rated V _{RRM} applied	1	70	_ A
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	2	00	
Maximum I ² t for fusing	I ² t	10 ms sine p	oulse, rated V _{RRM} applied	14	44	A ² s
Maximum 1-t for fusing	121	10 ms sine pulse, no voltage reapplied		2	00	A-S
Maximum $I^2 \sqrt{t}$ for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied		20	000	A²√s
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °C		1	.4	V
On-state slope resistance	r _t	T _{.I} = 125 °C		24	1.0	mΩ
Threshold voltage	V _{T(TO)}	1j=125 C		1	.1	V
Maximum rayaya and divact lackage current	1 /1	T _J = 25 °C	V Peter V A	0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_{\rm J} = 125 ^{\circ}{\rm C}$ $V_{\rm R} = {\rm Rated} {\rm V}_{\rm RRM} / {\rm V}_{\rm DRM}$		1	0	
Holding current	l _H	Anode supply = 6 V, resistive load, initial I _T = 1 A 16TTS08FP, 16TTS12FP		-	100	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load		2	00	
Maximum rate of rise of off-state voltage	dV/dt			5	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P_{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Maximum peak positive gate current	+ I _{GM}		1.5	Α	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, T _J = - 10 °C	90		
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	60	mA	
		Anode supply = 6 V, resistive load, T _J = 125 °C	35		
		Anode supply = 6 V, resistive load, T _J = - 10 °C	3.0		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	v	
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0]	
Maximum DC gate voltage not to trigger	V_{GD}	$T_{J} = 125 ^{\circ}\text{C}, V_{DRM} = \text{Rated value}$			
Maximum DC gate current not to trigger	I_{GD}			mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9			
Typical reverse recovery time	t _{rr}	T,i = 125 °C	4	μs		
Typical turn-off time	tq	1J = 125 C	110			

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THERMAL AND MECH	THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth and greased	1.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking device			Coop et de TO 200AB FULL BAK (04/1/0)	16TTS	D8FP
			Case style TO-220AB FULL-PAK (94/V0)	16TTS12FP	

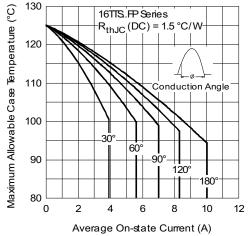


Fig. 1 - Current Rating Characteristics

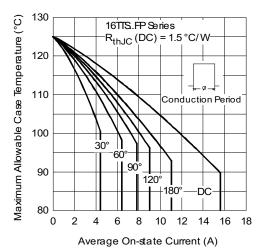


Fig. 2 - Current Rating Characteristics

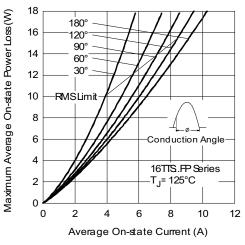


Fig. 3 - On-State Power Loss Characteristics

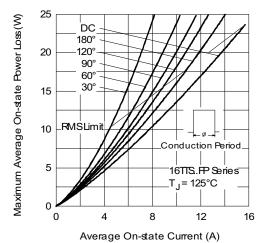


Fig. 4 - On-State Power Loss Characteristics

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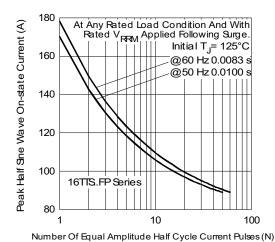


Fig. 5 - Maximum Non-Repetitive Surge Current

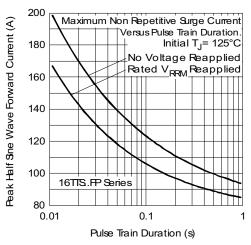
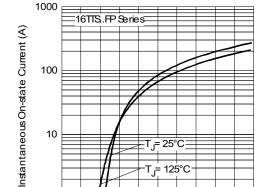


Fig. 6 - Maximum Non-Repetitive Surge Current



Instantaneous On-state Voltage (V)

3

5

2

0

Fig. 7 - On-State Voltage Drop Characteristics

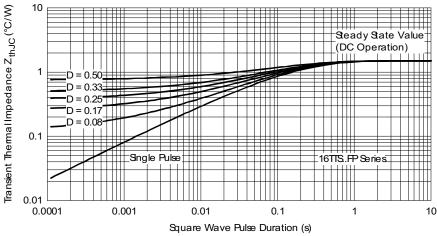
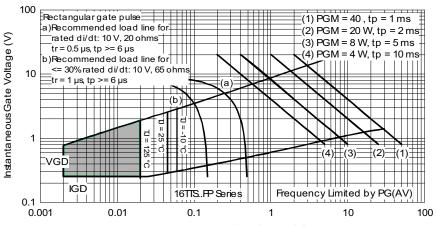


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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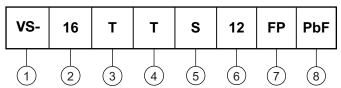
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Instantaneous Gate Current (A)
Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating, RMS value

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V_{RRM} - 08 = 800 V 12 = 1200 V

7 - FULL-PAK

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

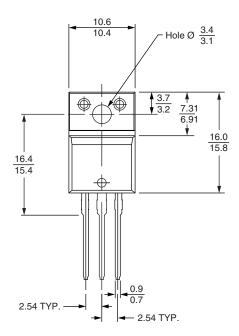
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08FPPbF	50	1000	Antistatic plastic tubes			
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12FPPbF	50	1000	Antistatic plastic tubes			
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes			

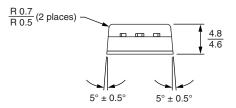
LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95072		
Dort marking information	TO-220FP PbF	www.vishay.com/doc?95069		
Part marking information	TO-220FP -M3	www.vishay.com/doc?95456		

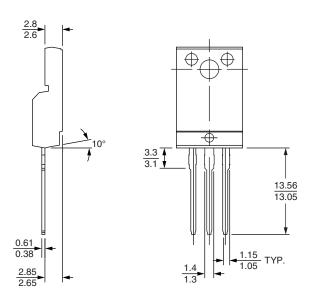


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DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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